

L Numb r	Hits	S arch Text	DB	Time stamp
-	1	(prism near5 pixel) and (tft or (thin near film near transistor)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:28
-	56	(prism near5 pixel) and (tft or (thin near film near transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:28
-	5	(prism near5 pixel) and (tft or (thin near film near transistor)) and organic and (insulating or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:30
-	1	(prism near5 pixel) and (tft or (thin near film near transistor)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:30
-	0	(prism near5 pixel).clm. and (tft or (thin near film near transistor)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:30
-	1	(prism near10 pixel).clm. and (tft or (thin near film near transistor)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:31
-	49	(prism near10 pixel).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:31
-	12	(prism near10 pixel).clm. and (tft or (thin near film near transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:33
-	49	(prism near10 pixel).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:33

-	121	(US-6522369-\$ or US-6518594-\$ or US-6512567-\$ or US-6466279-\$ or US-6392730-\$ or US-6388725-\$ or US-6277679-\$ or US-6208399-\$ or US-6072450-\$ or US-6468844-\$ or US-6521525-\$ or US-6351010-\$ or US-6459124-\$ or US-6013928-\$ or US-6128060-\$ or US-6346718-\$ or US-6103558-\$ or US-5781254-\$ or US-6461885-\$ or US-6351078-\$ or US-6243146-\$ or US-6262784-\$ or US-6057896-\$ or US-6545320-\$ or US-6420200-\$ or US-6407430-\$).did. or (US-6410368-\$ or US-6384427-\$ or US-5751381-\$ or US-6303963-\$ or US-5706064-\$ or US-6061105-\$ or US-6437367-\$ or US-5946059-\$ or US-5495353-\$ or US-5899547-\$ or US-5204659-\$ or US-6115099-\$ or US-6392622-\$ or US-5063378-\$ or US-6525788-\$ or US-5684365-\$ or US-6380559-\$ or US-6541294-\$ or US-6420758-\$ or US-6426245-\$ or US-6501132-\$ or US-6524877-\$ or US-6508686-\$ or US-6111270-\$ or US-6271543-\$ or US-6115090-\$ or US-6243153-\$).did. or (US-6420988-\$ or US-6521912-\$ or US-6440877-\$ or US-5612228-\$ or US-5719033-\$ or US-6013929-\$ or US-6300987-\$ or US-6524876-\$ or US-6509939-\$ or US-6285431-\$ or US-6515728-\$ or US-6038003-\$ or US-6411346-\$ or US-6429057-\$ or US-6287899-\$ or US-6313898-\$ or US-6335276-\$ or US-6001539-\$ or US-6256077-\$ or US-6515719-\$ or US-6380006-\$ or US-6156583-\$ or US-6337723-\$ or US-6037718-\$ or US-6023075-\$ or US-5681756-\$ or US-5883682-\$).did. or (US-6300152-\$ or US-6535535-\$ or US-6506635-\$ or US-6393042-\$ or US-6459108-\$ or US-6350680-\$ or US-5926235-\$ or US-6232625-\$ or US-5622814-\$ or US-6469755-\$ or US-6300612-\$ or US-6144426-\$ or US-6266111-\$ or US-5151801-\$ or US-5602679-\$ or US-5764319-\$ or US-5764323-\$).did. or (US-20030057419-\$ or US-20010025958-\$ or US-20010015441-\$ or US-20010004280-\$ or US-20010001567-\$ or US-20020063253-\$ or US-20020159016-\$ or US-20020075424-\$ or US-20020037646-\$).did. or	USPAT; US-PGPUB; JPO; DERWENT	2004/01/08 14:33
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-	212	prism and pixel and electrode and (tft or (thin near film near transistor)) and channel and passivation and organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:34
-	211	prism and pixel and electrode and (tft or (thin near film near transistor)) and channel and passivation and organic and (insulating or insulation or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:34
-	80	prism and pixel and electrode and (tft or (thin near film near transistor)) and channel and passivation and organic and (insulating or insulation or dielectric) and pixel.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:35
-	1	prism and pixel and electrode and (tft or (thin near film near transistor)) and channel and passivation and organic and (insulating or insulation or dielectric) and pixel.clm. and prism.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:35
-	16	prism and pixel and electrode and (tft or (thin near film near transistor)) and channel and (insulating or insulation or dielectric) and pixel.clm. and prism.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:37
-	10	prism and pixel and electrode and (tft or (thin near film near transistor)) and channel and (insulating or insulation or dielectric) and pixel.clm. and prism.clm. and (prism near10 pixel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:40
-	4	prism and pixel and electrode and (tft or (thin near film near transistor)) and channel and (insulating or insulation or dielectric) and pixel.clm. and prism.clm. and (prism near10 pixel).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:40
-	0	prism and pixel and electrode and (tft or (thin near film near transistor)) and channel and (insulating or insulation or dielectric) and pixel.clm. and prism.clm. and (prism near10 pixel).ti,ab,clm. and organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:41
-	1	prism near10 pixel near10 uneven	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:41
-	21393	pixel.clm. and pixel lab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:42

-	29	pixel.clm. and pixel.ab. and (pixel near10 prism).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:42
-	4	pixel.clm. and pixel.ab. and (pixel near10 prism).ti,ab,clm. and electrode.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:43
-	1289	prism and pixel and electrode and (tft or (thin near film near transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:43
-	63	prism and pixel and electrode and (tft or (thin near film near transistor)) and (pixel near10 prism)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:44
-	52	prism and pixel and electrode and (tft or (thin near film near transistor)) and (pixel near10 prism) and pixel.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:44
-	36	prism and pixel and electrode and (tft or (thin near film near transistor)) and (pixel near10 prism) and pixel.ti,ab,clm. and prism.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:45
-	9	prism and pixel and electrode and (tft or (thin near film near transistor)) and (pixel near10 prism) and pixel.ti,ab,clm. and prism.ti,ab,clm. and (pixel same (tft or (thin near film near transistor)) same prism)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:46
-	0	prism and pixel and electrode and (tft or (thin near film near transistor)) and (pixel near10 prism) and pixel.ti,ab,clm. and prism.ti,ab,clm. and (pixel same (tft or (thin near film near transistor)) same prism) and (insulating or insulation or dielectric) and organic and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:48
-	612	uneven adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:49
-	16	(uneven adj layer) same pixel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:49

-	0	(un v n adj layer) same pixel same prism	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:49
-	3	(prism near10 pixel).ti,ab,clm. and (tft or (thin near film near transistor)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:52
-	86	(prism near10 pixel) and (tft or (thin near film near transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:52
-	14	(prism near10 (pixel near electrode)) and (tft or (thin near film near transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:52
-	13	(prism near10 (pixel near electrode)) and (tft or (thin near film near transistor)) and pixel.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:55
-	10	(prism near10 (pixel near electrode)) and (tft or (thin near film near transistor)) and pixel.ti,ab,clm. and prism.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:53
-	2	(prism near10 (pixel near electrode)) and (tft or (thin near film near transistor)).ti,ab,clm. and pixel.ti,ab,clm. and prism.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:53
-	2	(prism near10 (pixel near electrode)) and (tft or (thin near film near transistor)) and pixel.ti,ab,clm. and (method or process).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:56
-	0	(prism near10 (pixel near electrode)) and (tft or (thin near film near transistor)) and pixel.ti,ab,clm. and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:56
-	4	(prism n ar10 (pixel near lectr de)) and (tft or (thin n ar film near transistor)) and pixel.ti,ab,clm. and gate and data	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 14:57